Group - E

- 8. (a) An amplifier has voltage gain of 500 without feedback. Calculate the voltage gain with negative feedback, given that the feedback ratio is 0.04.
  - (b) Write short notes on any three:
    - (i) Fermi Dirac distribution principle
    - (ii) Mass Action Law
    - (iii) Moore's Law
    - (iv) Barkhausen criterion
    - (v) LED.

 $3 + (3 \times 3) = 12$ 

- 9. (a) Explain the concept of virtual ground in an OPAMP. How is it different from a 'real' ground?
  - (b) Draw the open loop characteristics of an OPAMP. Show how an OPAMP can be used as a voltage comparator.

5 + (2 + 5) = 12

### B.TECH/AEIE/CSE/ECE/IT/2ND SEM/ECEN 1011/2019

# BASIC ELECTRONICS (ECEN 1011)

Time Allotted : 3 hrs

Full Marks : 70

Figures out of the right margin indicate full marks.

*Candidates are required to answer Group A and <u>any 5 (five)</u> from Group B to E, taking <u>at least one</u> from each group.* 

Candidates are required to give answer in their own words as far as practicable.

## Group – A (Multiple Choice Type Questions)

1. Choose the correct alternative for the following:

10 × 1 = 10

- (i) Zener breakdown occurs
  (a) mostly in Germanium junctions
  (b) due to rupture of covalent bonds
  (c) in lightly doped junctions
  (d) due to thermally generated minority carriers.
- (ii) With increase of temperature in a p-n junction diode
  - (a) Zener breakdown voltage increases while Avalanche breakdown voltage decreases
  - (b) Both Zener breakdown voltage and Avalanche breakdown voltage decrease
  - (c) Both Zener breakdown voltage and Avalanche breakdown voltage increase
  - (d) Zener breakdown voltage decreases while Avalanche breakdown voltage increases.
- (iii) The Q-point in a voltage amplifier is selected in the middle of the active region because
  - (a) it gives better stability
  - (b) the circuit needs a small dc voltage
  - (c) the biasing circuit then needs less number of resistors
  - (d) it gives distortion less output.
- (iv) When the base width of a BJT becomes zero, the transistor is said to be in
   (a) punch through
   (b) cut off
   (c) saturation
   (d) breakdown.

ECEN 1011

ECEN 1011

1

#### B.TECH/AEIE/CSE/ECE/IT/2ND SEM/ECEN 1011/2019

- In energy band diagram of n-type semiconductor, the donor energy (v) level is (a) slightly below conduction band (b) in conduction band (c) slightly above valence band (d) in valence band. In a bridge rectifier, if  $V_m$  is the peak voltage across the secondary, (vi) the PIV is (a) V<sub>m</sub> (b) 2V<sub>m</sub> (d)  $V_{\rm m}/\sqrt{2}$ . (c)  $V_m/2$ The CMRR of an ideal op amp is (vii) (a) zero (b) infinity (c) less than unity (d) greater than unity. The output of an integrator, for a step input is (viii) (b) a triangular waveform (a) a ramp (c) a spike (d) a pulse. Positive feedback is used in (ix)(a) amplifiers (b) oscillators (c) rectifiers (d) detectors.
- (x) The maximum rectification efficiency in case of full wave rectifier is
  (a) 100%
  (b) 81.2%
  (c) 66.6%
  (d) 40.6%.

### Group - B

- 2. (a) Explain the operation of a centre tapped full wave rectifier with the help of a circuit diagram.
  - (b) The forward resistance  $R_F$  of a diode is  $20\Omega$ . This diode is used in a half wave rectifier circuit. The applied input voltage is  $v = 50\sin \omega t$  and load resistance  $R_L$  is  $800 \Omega$ .
    - Determine: (i) The dc load current
      - (ii) The dc power output
      - (iii) Rectification efficiency

6 + 6 = 12

7 + 5 = 12

- 3. (a) Show how a Zener diode can be used as a reference diode in a circuit.
  - (b) A 12V, 0.36W Zener diode operates at a minimum current of 2mA. It is connected to a supply voltage of 15V with a series resistance R and a load resistance  $R_L$ . Calculate R and the range over which  $R_L$  can be varied.

B.TECH/AEIE/CSE/ECE/IT/2ND SEM/ECEN 1011/2019

Group - C

- 4. (a) Why is the emitter region of a transistor more heavily doped than the base?
  - (b) Draw the common-base input characteristics of a transistor and explain the Early effect.
  - (c) An n-p-n transistor with  $\alpha$  of 0.98 is operated in the CB mode. Calculate the base current and the collector current if the emitter current is 3mA and the reverse saturation current is 10µA.

2 + 6 + 4 = 12

- 5. (a) What is transistor biasing? Mention the factors for determining the choice of the quiescent point.
  - (b) What is thermal runaway in BJTs? Justify the use of a self-bias circuit in improving the circuit stability.

(2+2) + (2+6) = 12

## Group - D

- 6. (a) Does any current flow through an n-channel enhancement and a depletion MOSFET with a zero gate-to-source voltage and a positive drain bias? Justify your answer. Draw the static characteristics of an n-channel MOSFET operated in both the enhancement and depletion modes.
  - (b) An n-channel enhancement mode MOSFET shows a saturation drain current of 5mA for  $V_{GS} = 8V$ . If the threshold voltage is 4V calculate the saturation drain current for  $V_{GS} = 10V$ .

(3 + 5) + 4 = 12

- 7. (a) When is the channel of a JFET said to be pinched off. Explain pinch of voltage with the help of appropriate illustration.
  - (b) Draw the drain characteristics of a JFET, indicate the different regions of operation and explain how it can be used as a Voltage Variable Resistor (VVR).

6 + 6 = 12

3